RELIABILITY REPORT

FOR

MAX1935ETAxx

PLASTIC ENCAPSULATED DEVICES

June 30, 2003

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.

SUNNYVALE, CA 94086

Written by

Jim Pedicord Quality Assurance Reliability Lab Manager Reviewed by

Bryan J. Preeshl Quality Assurance Executive Director

Conclusion

The MAX1935 sucessfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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I. Device Description

A. General

The MAX1935 low-dropout linear regulator operates from a 2.25V to 5.5V supply and delivers a guaranteed 500mA load current with low 175mV dropout. The high-accuracy (±1.5%) output voltage is preset at an internally trimmed voltage or can be adjusted from 0.8V to 4.5V with an external resistive-divider.

An internal PMOS pass transistor allows low 210µA supply current, making this device ideal for portable equipment such as personal digital assistants (PDAs), cellular phones, cordless phones, and other equipment, including base stations and docking stations.

Other features include an active-low, power-OK output that indicates when the output is out of regulation, a 0.02µA shutdown mode, short-circuit protection, and thermal-shutdown protection. The MAX1935 comes in a tiny 1.9W, 8-pin 3mm x 3mm thin QFN package.

24.4mW/°C

B. Absolute Maximum Ratings

8-Pin Thin QFN

Item	Rating

IN, SHDN, POK, SET to GND -0.3V to +6V -0.3V to (VIN + 0.3V)OUT to GND Output Short-Circuit Duration Continuous Operating Temperature -40°C to +85°C +150°C Junction Temperature Storage Temperature Range -65°C to +150°C Lead Temperature (soldering, 10s) +300°C Continuous Power Dissipation (TA = $+70^{\circ}$ C) 8-Pin Thin QFN 1950mW Derates above +70°C

II. Manufacturing Information

A. Description/Function: 500mA, Low-Voltage Linear Regulator in Tiny QFN

B. Process: B8 (Standard .8 micron Silicon Gate CMOS)

C. Number of Device Transistors: 3282

D. Fabrication Location: California, USA

E. Assembly Location: Thailand

F. Date of Initial Production: October, 2002

III. Packaging Information

A. Package Type: 8-Pin Thin QFN

B. Lead Frame: Copper

C. Lead Finish: Solder Plate

D. Die Attach: Silver-Filled Epoxy

E. Bondwire: Gold (1.3 mil dia.)

F. Mold Material: Epoxy with silica filler

G. Assembly Diagram: # 05-2301-0139

H. Flammability Rating: Class UL94-V0

Classification of Moisture Sensitivity per JEDEC standard JESD22-A112:

Level 1

IV. Die Information

A. Dimensions: 56 x 56 mils

B. Passivation: Si₃N₄/SiO₂ (Silicon nitride/ Silicon dioxide)

Aluminum/Copper/Silicon C. Interconnect:

D. Backside Metallization: None

E. Minimum Metal Width: .8 microns (as drawn)

F. Minimum Metal Spacing: .8 microns (as drawn)

G. Bondpad Dimensions: 5 mil. Sq.

H. Isolation Dielectric: SiO₂

I. Die Separation Method: Wafer Saw

V. Quality Assurance Information

A. Quality Assurance Contacts:

Jim Pedicord (Manager, Reliability Operations)

Bryan Preeshl (Executive Director of QA)

Kenneth Huening (Vice President)

B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.

0.1% For all Visual Defects.

C. Observed Outgoing Defect Rate: < 50 ppm

D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in **Table 1**. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \text{ x } 4389 \text{ x } 155 \text{ x } 2}$$
(Chi square value for MTTF upper limit)
$$\frac{1}{192 \text{ x } 4389 \text{ x } 155 \text{ x } 2}$$
Thermal acceleration factor assuming a 0.8eV activation energy
$$\lambda = 7.01 \text{ x } 10^{-9}$$

$$\lambda = 7.01 \text{ F.I.T.}$$
 (60% confidence level @ 25°C)

This low failure rate represents data collected from Maxim's reliability qualification and monitor programs. Maxim also performs weekly Burn-In on samples from production to assure the reliability of its processes. The reliability required for lots which receive a burn-in qualification is 59 F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on lots exceeding this level. The following Burn-In Schematic (Spec. #06-5751) shows the static circuit used for this test. Maxim also performs 1000 hour life test monitors quarterly for each process. This data is published in the Product Reliability Report (RR-1M).

B. Moisture Resistance Tests

Maxim evaluates pressure pot stress from every assembly process during qualification of each new design. Pressure Pot testing must pass a 20% LTPD for acceptance. Additionally, industry standard 85°C/85%RH or HAST tests are performed quarterly per device/package family.

C. E.S.D. and Latch-Up Testing

The PY37 die type has been found to have all pins able to withstand a transient pulse of 2000V, per Mil-Std-883 Method 3015 (reference attached ESD Test Circuit). Latch-Up testing has shown that this device withstands a current of ± 250 mA.

Table 1 Reliability Evaluation Test Results

MAX1935ETAxx

TEST ITEM	TEST CONDITION	FAILURE		SAMPLE	NUMBER OF
1201112	1201 00115111011	IDENTIFICATION	PACKAGE	SIZE	FAILURES
Static Life Test (Note 1)					
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality		155	0
Moisture Testing	g (Note 2)				
Pressure Pot	Ta = 121°C P = 15 psi. RH= 100% Time = 168hrs.	DC Parameters & functionality		77	0
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality		77	0
Mechanical Stre	ess (Note 2)				
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality		77	0

Note 1: Life Test Data may represent plastic DIP qualification lots. Note 2: Generic Package/Process data

Attachment #1

TABLE II. Pin combination to be tested. 1/2/

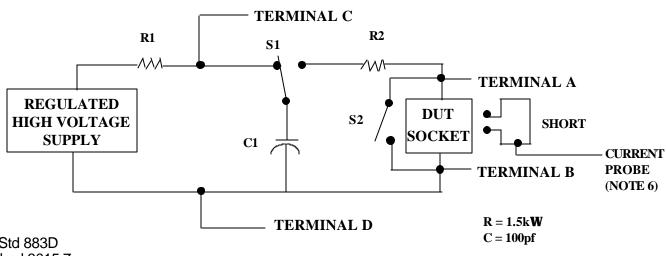
	Terminal A (Each pin individually connected to terminal A with the other floating)	Terminal B (The common combination of all like-named pins connected to terminal B)
1.	All pins except V _{PS1} 3/	All V _{PS1} pins
2.	All input and output pins	All other input-output pins

- 1/ Table II is restated in narrative form in 3.4 below.
- 2/ No connects are not to be tested.
- 3/ Repeat pin combination I for each named Power supply and for ground

(e.g., where V_{PS1} is V_{DD} , V_{CC} , V_{SS} , V_{BB} , GND, $+V_{S}$, $-V_{S}$, V_{REF} , etc).

3.4 Pin combinations to be tested.

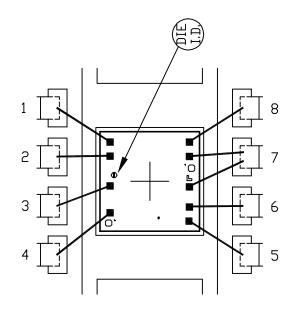
- a. Each pin individually connected to terminal A with respect to the device ground pin(s) connected to terminal B. All pins except the one being tested and the ground pin(s) shall be open.
- b. Each pin individually connected to terminal A with respect to each different set of a combination of all named power supply pins (e.g., V_{SS1} , or V_{SS2} or V_{CC1} , or V_{CC2}) connected to terminal B. All pins except the one being tested and the power supply pin or set of pins shall be open.
- c. Each input and each output individually connected to terminal A with respect to a combination of all the other input and output pins connected to terminal B. All pins except the input or output pin being tested and the combination of all the other input and output pins shall be open.



Mil Std 883D Method 3015.7 Notice 8

3x3x0.8 MM QFN THIN PKG.

EXPOSED PAD PKG.



PKG. CODE: T833-1		SIGNATURES	DATE	CONFIDENTIAL & PROPRIETAR	
CAV./PAD SIZE:	PKG.			BOND DIAGRAM #:	REV:
71×102	DESIGN			05-2301-0139	В

